

PATENT3A
2/25/01IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Vincent Derycke et al.

Title: MONOATOMIC AND MONOCRYSTALLINE LAYER
OF LARGE SIZE, IN DIAMOND TYPE
CARBON, AND METHOD FOR THE
MANUFACTURE OF THIS LAYER

Docket No.: 33585

PRELIMINARY AMENDMENTAssistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to the examination of the above-identified patent application, it is requested that the following amendments be made.

IN THE CLAIMS:

Please amend claims 1, 2, 4 - 9 and 11 as follows:

1 1. (Amended) Monoatomic and monocrystalline layer
2 of diamond type carbon, this layer being characterized
3 in that it is formed on the surface of a monocrystalline
4 substrate of SiC and extends closely over the totality of
5 this substrate.

1 2. (Amended) Monoatomic and monocrystalline layer
2 according to claim 1, the SiC monocrystalline substrate
3 being a thin layer of monocrystalline SiC in cubic phase
4 β -SiC formed on a platelet of Si, the monoatomic and